









Bill of Materials

Designator	Description	Value	Q
C1	Electrolytic capacitor 16v/50v	10µF	1
C2, C3, C4	Ceramic or tantalum capacitor	100nF	3
MEM1, MEM2, MEM3	EEProm 64K, 8K x 8 bits	AT28C64	3
P1	Pin Header, THT, pitch 2.54mm, Dual Row, Vertical, 16p	16P	1
P2	Pin Header, THT, pitch 2.54mm, Dual Row, Vertical, 32p	32p	1
P3, P6	WR-PHD Pin Header, THT, pitch 2.54mm, Dual Row, Vertical, 8p	8p	2
P4	Pin Header, THT, pitch 2.54mm, Dual Row, Vertical, 24p	24p	1
RN4, RN5, RN6	Resistor array 8 elements,9 pins	330Ω	3



Assembly List

Desig.	Description	Value
C1	Electrolytic capacitor 16v/50v	10µF
C2	Ceramic or tantalum capacitor	100nF
C3	Ceramic or tantalum capacitor	100nF
C4	Ceramic or tantalum capacitor	100nF
MEM1	EEProm 64K, 8K x 8 bits	AT28C64
MEM2	EEProm 64K, 8K x 8 bits	AT28C64
MEM3	EEProm 64K, 8K x 8 bits	AT28C64
P1	Pin Header, THT, pitch 2.54mm, Dual Row, Vertical, 16p	16P
P2	Pin Header, THT, pitch 2.54mm, Dual Row, Vertical, 32p	32p
P3	WR-PHD Pin Header, THT, pitch 2.54mm, Dual Row, Vertical, 8p	8p
P4	Pin Header, THT, pitch 2.54mm, Dual Row, Vertical, 24p	24p
P6	WR-PHD Pin Header, THT, pitch 2.54mm, Dual Row, Vertical, 8p	8p
RN4	Resistor array 8 elements,9 pins	330Ω
RN5	Resistor array 8 elements,9 pins	330Ω
RN6	Resistor array 8 elements,9 pins	330Ω